

Simultaneous current-, force- and work function measurements

Ch. Schiller, M. Herz, F. J. Giessibl, J. Mannhart

Universität Augsburg, Experimentalphysik VI, EKM, Universitätsstr. 1, 86135 Augsburg

Christian.Schiller@physik.uni-augsburg.de

In principle the local work function of a surface determines the spatial decay of the charge density at the Fermi level normal to the surface. First, a method is presented that enables simultaneous measurements of local work function and tip-sample forces [1]. A combined dynamic STM and AFM is used to measure the tunnelling current between an oscillating tip and the sample in real time as a function of the cantilever's deflection as well as the frequency shift that results from the tip-sample forces. We used various qPlus sensors with a k of at least 1800 N/m for stable operation at small amplitudes. The high stiffness is required to comply with the stability criteria in frequency modulation (FM) AFM [2]. Amplitudes in the sub-Å range are required such that I remains above the noise level of the current amplifier even when the tip is at the far point of the surface. The presented method is a combination of 'current-imaging-tunnelling-spectroscopy' introduced by Pethica et al. [3] and FM-AFM.

Figure 1 contains a simultaneous measurement of topography (constant average current), decay constant κ of the tunnelling current, frequency shift Δf and damping signal ΔE_C per oscillation cycle on a silicon (111)-(7x7) surface in UHV. Figure 1 shows that while all adatoms appear bright in the frequency shift image c), κ shown in b) displays a contrast inversion on the two halves of the Si unit cell. Currently, we adapt this technique to investigate the electronic states of oxide surfaces such as TiO₂.

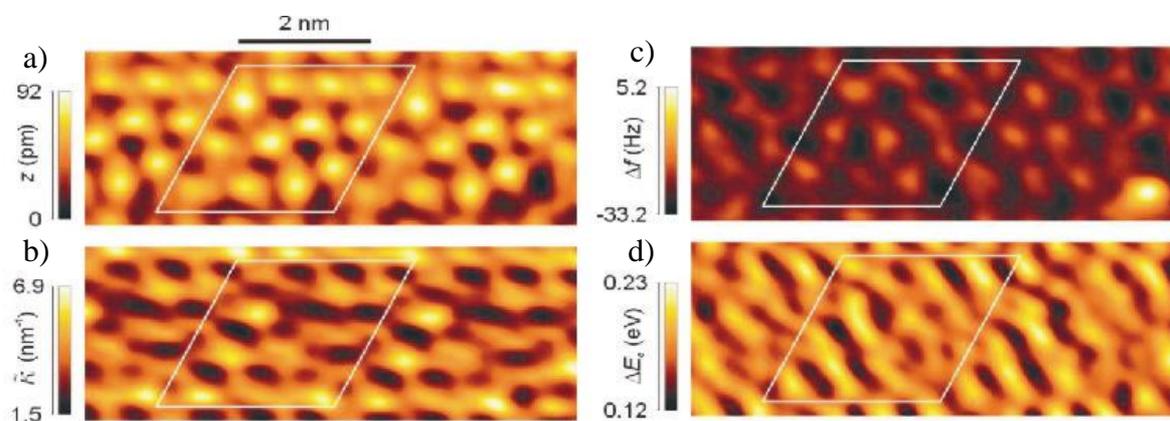


Fig.1 Simultaneous current-, force- and work function measurement with atomic resolution on silicon (111)-(7x7) with a tungsten tip and a qPlus sensor with a quality factor of $Q = 2240$; the surface cell is indicated with white diamonds;

a) topography; b) work function; c) frequency shift; d) damping

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- [3] J.B. Pethica, J. Knall, J.H. Wilson, Inst. Of Physics Conf. Ser., London **134**, 597 (1993)